Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, PWM, WDT
Number of I/O	82
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l471vet6tr

3.4 Embedded Flash memory

STM32L471xx devices feature up to 1 Mbyte of embedded Flash memory available for storing programs and data. The Flash memory is divided into two banks allowing read-while-write operations. This feature allows to perform a read operation from one bank while an erase or program operation is performed to the other bank. The dual bank boot is also supported. Each bank contains 256 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
  - Level 0: no readout protection
  - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
  - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Table 3. Access status versus readout protection level and execution modes

Area	Protection level	User execution			Debug, boot from RAM or boot from system memory (loader)		
		Read	Write	Erase	Read	Write	Erase
Main memory	1	Yes	Yes	Yes	No	No	No
	2	Yes	Yes	Yes	N/A	N/A	N/A
System memory	1	Yes	No	No	Yes	No	No
	2	Yes	No	No	N/A	N/A	N/A
Option bytes	1	Yes	Yes	Yes	Yes	Yes	Yes
	2	Yes	No	No	N/A	N/A	N/A
Backup registers	1	Yes	Yes	N/A(1)	No	No	N/A(1)
	2	Yes	Yes	N/A	N/A	N/A	N/A
SRAM2	1	Yes	Yes	Yes(1)	No	No	No(1)
	2	Yes	Yes	Yes	N/A	N/A	N/A

1. Erased when RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas per bank can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. One area per bank can be selected, with 64-bit granularity. An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

Table 4. STM32L471 modes overview (continued)

Mode	Regulator (1)	CPU	Flash	SRAM	Clocks	DMA & Peripherals(2)	Wakeup source	Consumption(3)	Wakeup time
Stop 1	LPR	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC,IWDG COMPx (x=1,2) DACx (x=1,2) OPAMPx (x=1,2) USARTx (x=1...5)(6) LPUART1(6) I2Cx (x=1...3)(7) LPTIMx (x=1,2) *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC,IWDG COMPx (x=1..2) USARTx (x=1...5)(6) LPUART1(6) I2Cx (x=1...3)(7) LPTIMx (x=1,2) SWPMI1(8)	6.6 µA w/o RTC 6.9 µA w RTC	4 µs in SRAM 6 µs in Flash
Stop 2	LPR	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC,IWDG COMPx (x=1..2) I2C3(7) LPUART1(6) LPTIM1 *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC,IWDG COMPx (x=1..2) I2C3(7) LPUART1(6) LPTIM1	1.1 µA w/o RTC 1.4 µA w/RTC	5 µs in SRAM 7 µs in Flash

Standby mode, supplied by the low-power Regulator (Standby with RAM2 retention mode).

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

The system clock after wakeup is MSI up to 8 MHz.

- **Shutdown** mode

  The Shutdown mode allows to achieve the lowest power consumption. The internal regulator is switched off so that the VCORE domain is powered off. The PLL, the HSI16, the MSI, the LSI and the HSE oscillators are also switched off.

  The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

  The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

  SRAM1, SRAM2 and register contents are lost except for registers in the Backup domain.

  The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper).

  The system clock after wakeup is MSI at 4 MHz.

- Transmission
  - Three transmit mailboxes
  - Configurable transmit priority
- Reception
  - Two receive FIFOs with three stages
  - 14 Scalable filter banks
  - Identifier list feature
  - Configurable FIFO overrun
- Time-triggered communication option
  - Disable automatic retransmission mode
  - 16-bit free running timer
  - Time Stamp sent in last two data bytes
- Management
  - Maskable interrupts
  - Software-efficient mailbox mapping at a unique address space

3.32 Secure digital input/output and MultiMediaCards Interface (SDMMC)

The card host interface (SDMMC) provides an interface between the APB peripheral bus and MultiMediaCards (MMCs), SD memory cards and SDIO cards.

The SDMMC features include the following:

- Full compliance with MultiMediaCard System Specification Version 4.2. Card support for three different databus modes: 1-bit (default), 4-bit and 8-bit
- Full compatibility with previous versions of MultiMediaCards (forward compatibility)
- Full compliance with SD Memory Card Specifications Version 2.0
- Full compliance with SD I/O Card Specification Version 2.0: card support for two different databus modes: 1-bit (default) and 4-bit
- Data transfer up to 48 MHz for the 8 bit mode
- Data write and read with DMA capability

3.33 Flexible static memory controller (FSMC)

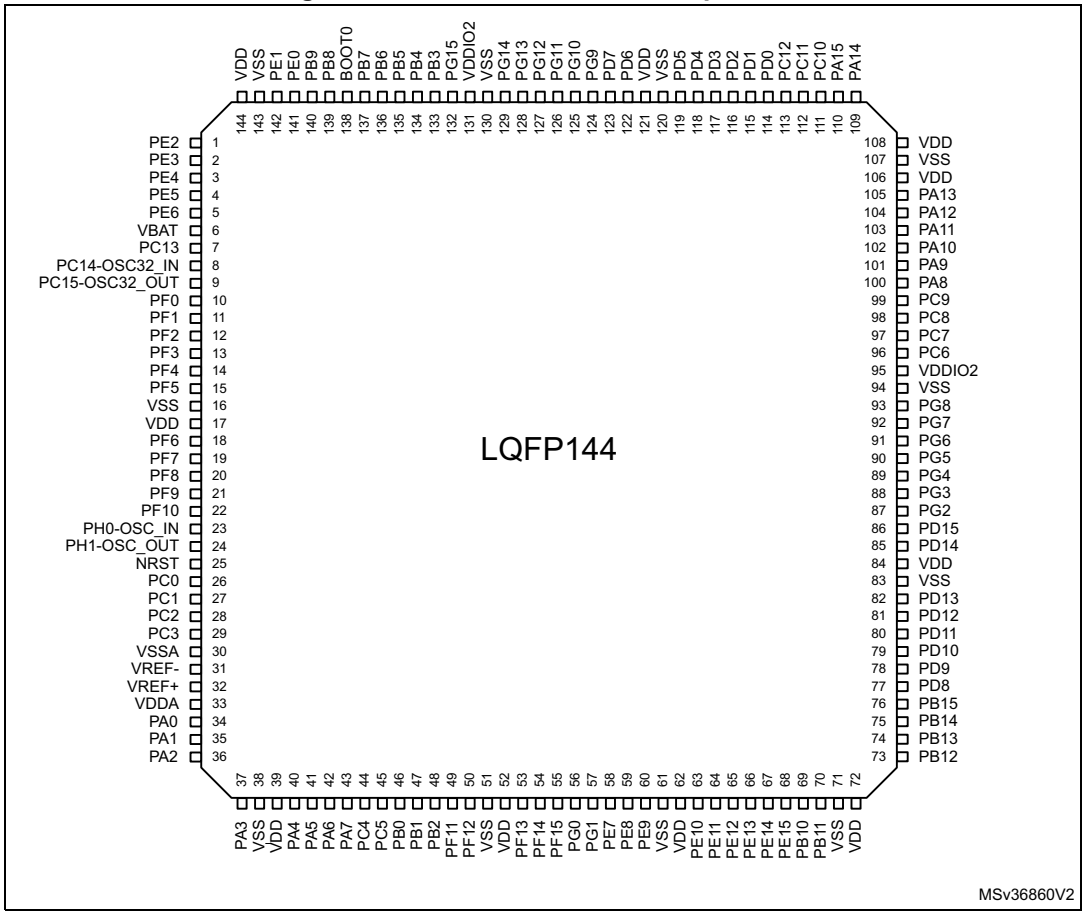
The Flexible static memory controller (FSMC) includes two memory controllers:

- The NOR/PSRAM memory controller
- The NAND/memory controller

This memory controller is also named Flexible memory controller (FMC).

4 Pinouts and pin description

Figure 5. STM32L471Zx LQFP144 pinout(1)



1. The above figure shows the package top view.

Table 15. STM32L471xx pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
14	23	L2	34	PA0	I/O	FT_a	-	TIM2_CH1, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, SAI1_EXTCLK, TIM2_ETR, EVENTOUT	OPAMP1_VINP, ADC12_IN5, RTC_TAMP2/WKUP1
-	-	M3	-	OPAMP1_VINM	I	TT	-	-	-
15	24	M2	35	PA1	I/O	FT_a	-	TIM2_CH2, TIM5_CH2, USART2_RTS_DE, UART4_RX, TIM15_CH1N, EVENTOUT	OPAMP1_VINM, ADC12_IN6
16	25	K3	36	PA2	I/O	FT_a	-	TIM2_CH3, TIM5_CH3, USART2_TX, SAI2_EXTCLK, TIM15_CH1, EVENTOUT	ADC12_IN7, WKUP4/LSCO
17	26	L3	37	PA3	I/O	TT	-	TIM2_CH4, TIM5_CH4, USART2_RX, TIM15_CH2, EVENTOUT	OPAMP1_ VOUT, ADC12_IN8
18	27	E3	38	VSS	S	-	-	-	-
19	28	H3	39	VDD	S	-	-	-	-
20	29	J4	40	PA4	I/O	TT_a	-	SPI1_NSS, SPI3_NSS, USART2_CK, SAI1_FS_B, LPTIM2_OUT, EVENTOUT	ADC12_IN9, DAC1_OUT1
21	30	K4	41	PA5	I/O	TT_a	-	TIM2_CH1, TIM2_ETR, TIM8_CH1N, SPI1_SCK, LPTIM2_ETR, EVENTOUT	ADC12_IN10, DAC1_OUT2
22	31	L4	42	PA6	I/O	FT_a	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, USART3_CTS, QUADSPI_BK1_IO3, TIM1_BKIN_COMP2, TIM8_BKIN_COMP2, TIM16_CH1, EVENTOUT	OPAMP2_VINP, ADC12_IN11
-	-	M4	-	OPAMP2_VINM	I	TT	-	-	-
23	32	J5	43	PA7	I/O	FT_a	-	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, SPI1_MOSI, QUADSPI_BK1_IO2, TIM17_CH1, EVENTOUT	OPAMP2_VINM, ADC12_IN12
24	33	K5	44	PC4	I/O	FT_a	-	USART3_TX, EVENTOUT	COMP1_INM, ADC12_IN13

Table 15. STM32L471xx pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	40	M8	60	PE9	I/O	FT	-	TIM1_CH1, DFSDM_CKOUT, FMC_D6, SAI1_FS_B, EVENTOUT	-
-	-	F6	61	VSS	S	-	-	-	-
-	-	G6	62	VDD	S	-	-	-	-
-	41	L8	63	PE10	I/O	FT	-	TIM1_CH2N, DFSDM_DATIN4, TSC_G5_IO1, QUADSPI_CLK, FMC_D7, SAI1_MCLK_B, EVENTOUT	-
-	42	M9	64	PE11	I/O	FT	-	TIM1_CH2, DFSDM_CKIN4, TSC_G5_IO2, QUADSPI_NCS, FMC_D8, EVENTOUT	-
-	43	L9	65	PE12	I/O	FT	-	TIM1_CH3N, SPI1_NSS, DFSDM_DATIN5, TSC_G5_IO3, QUADSPI_BK1_IO0, FMC_D9, EVENTOUT	-
-	44	M10	66	PE13	I/O	FT	-	TIM1_CH3, SPI1_SCK, DFSDM_CKIN5, TSC_G5_IO4, QUADSPI_BK1_IO1, FMC_D10, EVENTOUT	-
-	45	M11	67	PE14	I/O	FT	-	TIM1_CH4, TIM1_BKIN2, TIM1_BKIN2_COMP2, SPI1_MISO, QUADSPI_BK1_IO2, FMC_D11, EVENTOUT	-
-	46	M12	68	PE15	I/O	FT	-	TIM1_BKIN, TIM1_BKIN_COMP1, SPI1_MOSI, QUADSPI_BK1_IO3, FMC_D12, EVENTOUT	-

3. For operation with voltage higher than Min (V_{DD}, V_{DDA}, V_{DDIO2}) +0.3 V, the internal Pull-up and Pull-Down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).
5. In low-power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 23* are derived from tests performed under the ambient temperature condition summarized in *Table 22*.

Table 23. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		10	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	µs/V
	V_{DDA} fall time rate		10	∞	
t_{VDDIO2}	V_{DDIO2} rise time rate	-	0	∞	µs/V
	V_{DDIO2} fall time rate		10	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 24* are derived from tests performed under the ambient temperature conditions summarized in *Table 22: General operating conditions*.

Table 24. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions(1)	Min	Typ	Max	Unit
$t_{RSTTEMPO}$(2)	Reset temporization after BOR0 is detected	V_{DD} rising	-	250	400	µs
V_{BOR0}(2)	Brown-out reset threshold 0	Rising edge	1.62	1.66	1.7	V
		Falling edge	1.6	1.64	1.69	
V_{BOR1}	Brown-out reset threshold 1	Rising edge	2.06	2.1	2.14	V
		Falling edge	1.96	2	2.04	
V_{BOR2}	Brown-out reset threshold 2	Rising edge	2.26	2.31	2.35	V
		Falling edge	2.16	2.20	2.24	
V_{BOR3}	Brown-out reset threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{BOR4}	Brown-out reset threshold 4	Rising edge	2.85	2.90	2.95	V
		Falling edge	2.76	2.81	2.86	
V_{PVD0}	Programmable voltage detector threshold 0	Rising edge	2.1	2.15	2.19	V
		Falling edge	2	2.05	2.1	

Table 29. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART enable (Cache ON Prefetch OFF)

Symbol	Parameter	Conditions			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	2.9	mA	111	µA/MHz
				Coremark	3.1		118	
				Dhrystone 2.1	3.1		119	
				Fibonacci	2.9		112	
				While(1)	2.8		108	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	10.2	mA	127	µA/MHz
				Coremark	10.9		136	
				Dhrystone 2.1	11.0		137	
				Fibonacci	10.5		131	
				While(1)	9.9		124	
I_{DD}(LPRun)	Supply current in Low-power run	$f_{HCLK} = f_{MSI}$ = 2 MHz all peripherals disable		Reduced code(1)	272	µA	136	µA/MHz
				Coremark	291		145	
				Dhrystone 2.1	302		151	
				Fibonacci	269		135	
				While(1)	269		135	

1. Reduced code used for characterization results provided in *Table 26*, *Table 27*, *Table 28*.

Table 41. Low-power mode wakeup timings(1) (continued)

Symbol	Parameter	Conditions		Typ	Max	Unit
$t_{WUSTOP1}$	Wake up time from Stop 1 mode to Run mode in Flash	Range 1	Wakeup clock MSI = 48 MHz	6.2	10.2	µs
			Wakeup clock HSI16 = 16 MHz	6.3	8.99	
		Range 2	Wakeup clock MSI = 24 MHz	6.3	10.46	
			Wakeup clock HSI16 = 16 MHz	6.3	8.87	
			Wakeup clock MSI = 4 MHz	8.0	13.23	
	Wake up time from Stop 1 mode to Run mode in SRAM1	Range 1	Wakeup clock MSI = 48 MHz	4.5	5.78	
			Wakeup clock HSI16 = 16 MHz	5.5	7.1	
		Range 2	Wakeup clock MSI = 24 MHz	5.0	6.5	
			Wakeup clock HSI16 = 16 MHz	5.5	7.1	
			Wakeup clock MSI = 4 MHz	8.2	13.5	
	Wake up time from Stop 1 mode to Low-power run mode in Flash	Regulator in low-power mode (LPR=1 in PWR_CR1)	Wakeup clock MSI = 2 MHz	12.7	20	
	Wake up time from Stop 1 mode to Low-power run mode in SRAM1			10.7	21.5	
$t_{WUSTOP2}$	Wake up time from Stop 2 mode to Run mode in Flash	Range 1	Wakeup clock MSI = 48 MHz	8.0	9.4	µs
			Wakeup clock HSI16 = 16 MHz	7.3	9.3	
		Range 2	Wakeup clock MSI = 24 MHz	8.2	9.9	
			Wakeup clock HSI16 = 16 MHz	7.3	9.3	
			Wakeup clock MSI = 4 MHz	10.6	15.8	
	Wake up time from Stop 2 mode to Run mode in SRAM1	Range 1	Wakeup clock MSI = 48 MHz	5.1	6.7	
			Wakeup clock HSI16 = 16 MHz	5.7	8	
		Range 2	Wakeup clock MSI = 24 MHz	5.5	6.65	
			Wakeup clock HSI16 = 16 MHz	5.7	7.53	
			Wakeup clock MSI = 4 MHz	8.2	16.6	
t_{WUSTBY}	Wakeup time from Standby mode to Run mode	Range 1	Wakeup clock MSI = 8 MHz	14.3	20.8	µs
			Wakeup clock MSI = 4 MHz	20.1	35.5	
$t_{WUSTBY\ SRAM2}$	Wakeup time from Standby with SRAM2 to Run mode	Range 1	Wakeup clock MSI = 8 MHz	14.3	24.3	µs
			Wakeup clock MSI = 4 MHz	20.1	38.5	
t_{WUSHDN}	Wakeup time from Shutdown mode to Run mode	Range 1	Wakeup clock MSI = 4 MHz	256	330.6	µs

1. Guaranteed by characterization results.

6.3.8 Internal clock source characteristics

The parameters given in *Table 47* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*. The provided curves are characterization results, not tested in production.

High-speed internal (HSI16) RC oscillator

Table 47. HSI16 oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	HSI16 Frequency	V_{DD}=3.0 V, T_A=30 °C	15.88	-	16.08	MHz
TRIM	HSI16 user trimming step	Trimming code is not a multiple of 64	0.2	0.3	0.4	%
		Trimming code is a multiple of 64	-4	-6	-8	
DuCy(HSI16)(2)	Duty Cycle	-	45	-	55	%
Δ_{Temp}(HSI16)	HSI16 oscillator frequency drift over temperature	T_A= 0 to 85 °C	-1	-	1	%
		T_A= -40 to 125 °C	-2	-	1.5	%
Δ_{VDD}(HSI16)	HSI16 oscillator frequency drift over V_{DD}	V_{DD}=1.62 V to 3.6 V	-0.1	-	0.05	%
t_{su}(HSI16)(2)	HSI16 oscillator start-up time	-	-	0.8	1.2	µs
t_{stab}(HSI16)(2)	HSI16 oscillator stabilization time	-	-	3	5	µs
I_{DD}(HSI16)(2)	HSI16 oscillator power consumption	-	-	155	190	µA

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 65. ADC accuracy - limited test conditions 1(1)(2)(3)

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, V_{DDA} = VREF+ = 3 V, TA = 25 °C	Single ended	Fast channel (max speed)	-	4	5	LSB
				Slow channel (max speed)	-	4	5	
			Differential	Fast channel (max speed)	-	3.5	4.5	
				Slow channel (max speed)	-	3.5	4.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	1	2.5	
				Slow channel (max speed)	-	1	2.5	
			Differential	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
EG	Gain error		Single ended	Fast channel (max speed)	-	2.5	4.5	
				Slow channel (max speed)	-	2.5	4.5	
			Differential	Fast channel (max speed)	-	2.5	3.5	
				Slow channel (max speed)	-	2.5	3.5	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1	1.5	
				Slow channel (max speed)	-	1	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
			Differential	Fast channel (max speed)	-	1	2	
				Slow channel (max speed)	-	1	2	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10.4	10.5	-	bits
				Slow channel (max speed)	10.4	10.5	-	
			Differential	Fast channel (max speed)	10.8	10.9	-	
				Slow channel (max speed)	10.8	10.9	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	64.4	65	-	dB
				Slow channel (max speed)	64.4	65	-	
			Differential	Fast channel (max speed)	66.8	67.4	-	
				Slow channel (max speed)	66.8	67.4	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	65	66	-	
				Slow channel (max speed)	65	66	-	
			Differential	Fast channel (max speed)	67	68	-	
				Slow channel (max speed)	67	68	-	

Quad SPI characteristics

Unless otherwise specified, the parameters given in *Table 83* and *Table 84* for Quad SPI are derived from tests performed under the ambient temperature, f_{AHB} frequency and V_{DD} supply voltage conditions summarized in *Table 22: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 15 or 20 pF
- Measurement points are done at CMOS levels: 0.5 x V_{DD}

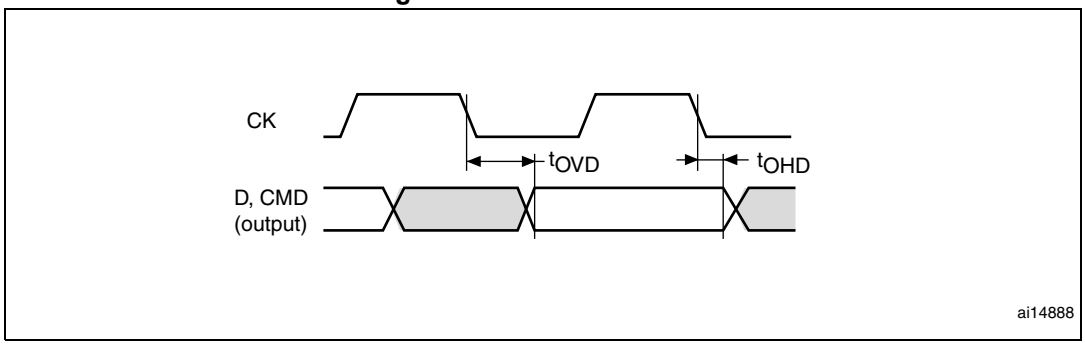
Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics.

Table 83. Quad SPI characteristics in SDR mode(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
F_{CK} $1/t_{(CK)}$	Quad SPI clock frequency	1.71 < V_{DD}< 3.6 V, C_{LOAD} = 20 pF Voltage Range 1	-	-	40	MHz
		1.71 < V_{DD}< 3.6 V, C_{LOAD} = 15 pF Voltage Range 1	-	-	48	
		2.7 < V_{DD}< 3.6 V, C_{LOAD} = 15 pF Voltage Range 1	-	-	60	
		1.71 < V_{DD} < 3.6 V C_{LOAD} = 20 pF Voltage Range 2	-	-	26	
$t_{w(CKH)}$	Quad SPI clock high and low time	f_{AHBCLK}= 48 MHz, presc=0	$t_{(CK)}/2$-2	-	$t_{(CK)}/2$	ns
$t_{w(CKL)}$			$t_{(CK)}/2$	-	$t_{(CK)}/2$+2	
$t_{s(IN)}$	Data input setup time	Voltage Range 1	4	-	-	
		Voltage Range 2	3.5	-	-	
$t_{h(IN)}$	Data input hold time	Voltage Range 1	5.5	-	-	
		Voltage Range 2	6.5	-	-	
$t_{v(OUT)}$	Data output valid time	Voltage Range 1	-	2.5	5	
		Voltage Range 2	-	3	5	
$t_{h(OUT)}$	Data output hold time	Voltage Range 1	1.5	-	-	
		Voltage Range 2	2	-	-	

1. Guaranteed by characterization results.

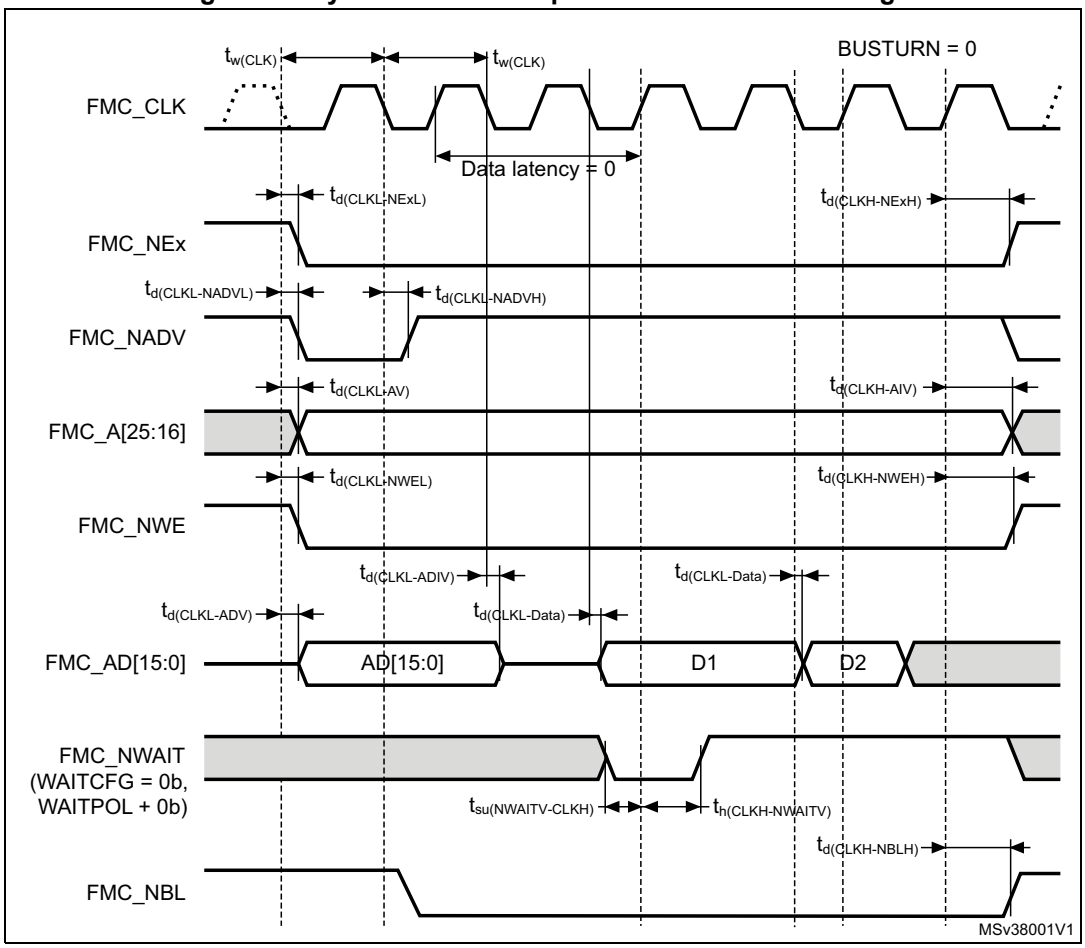
Figure 35. SD default mode



CAN (controller area network) interface

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

Figure 41. Synchronous multiplexed PSRAM write timings

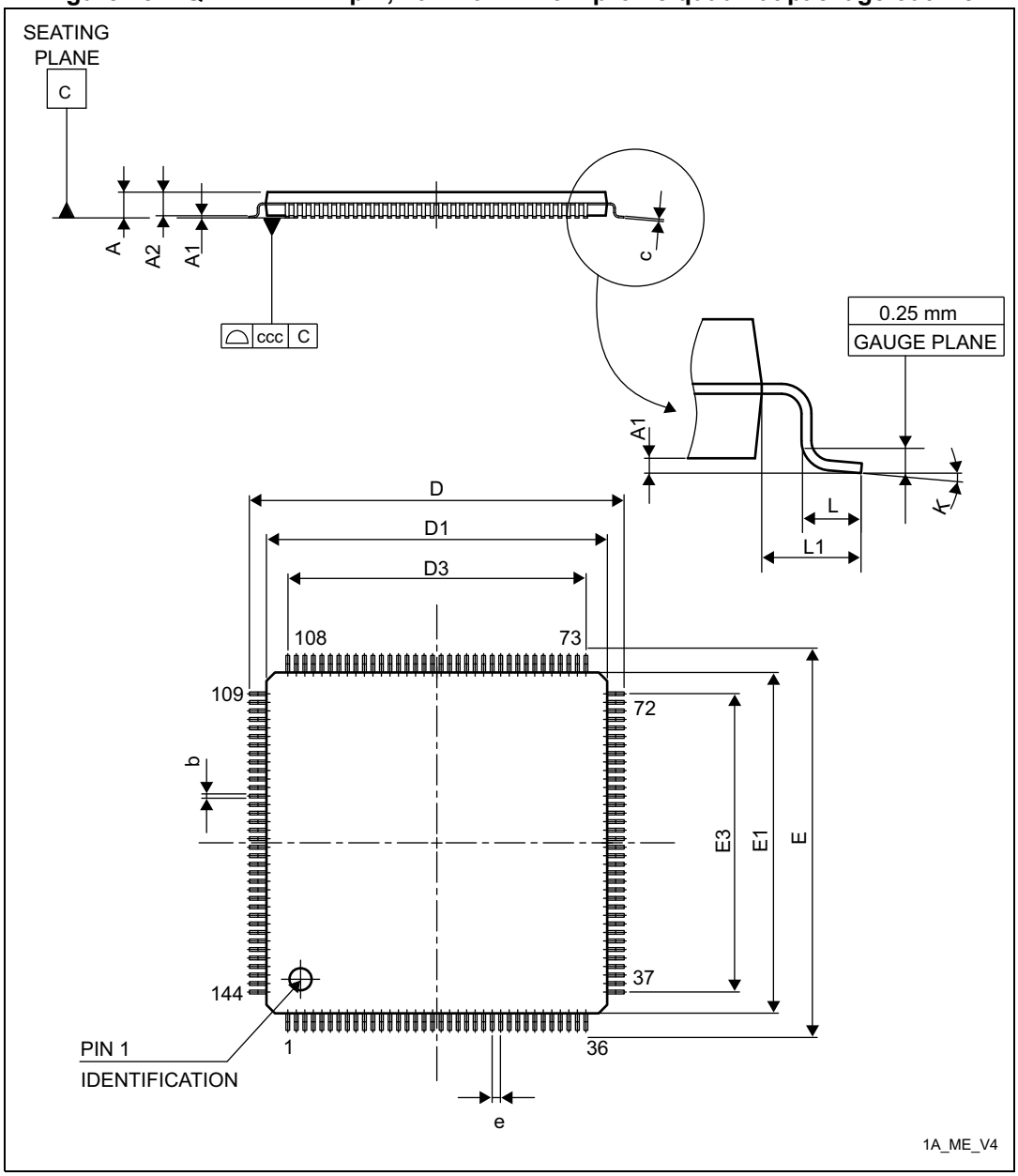


7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

7.1 LQFP144 package information

Figure 48. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 103. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	0.080	-	-	0.0031	-
eee	-	0.150	-	-	0.0059	-
fff	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 52. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package recommended footprint

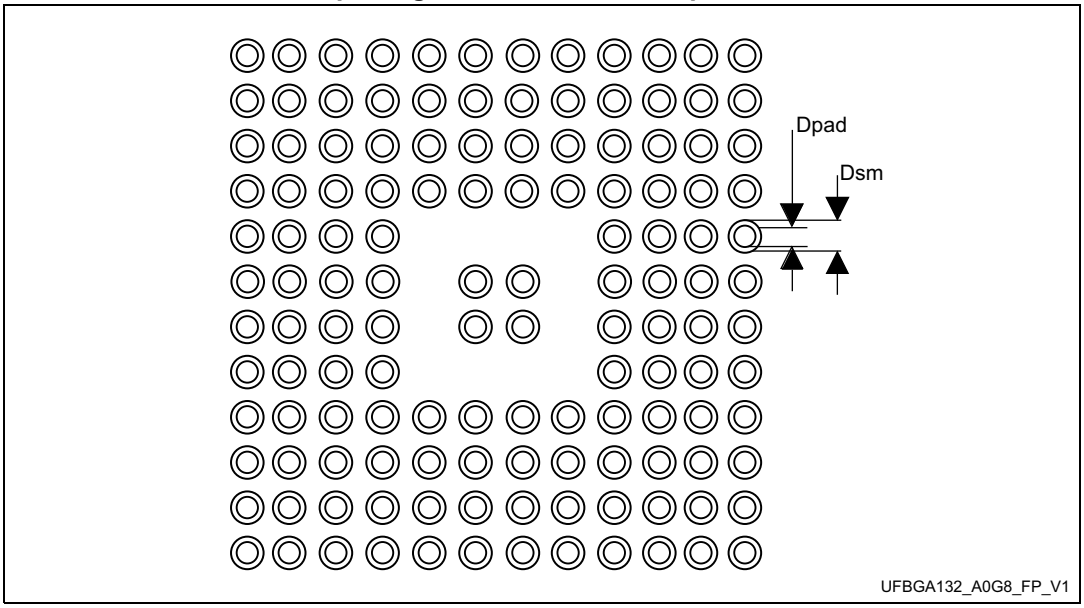
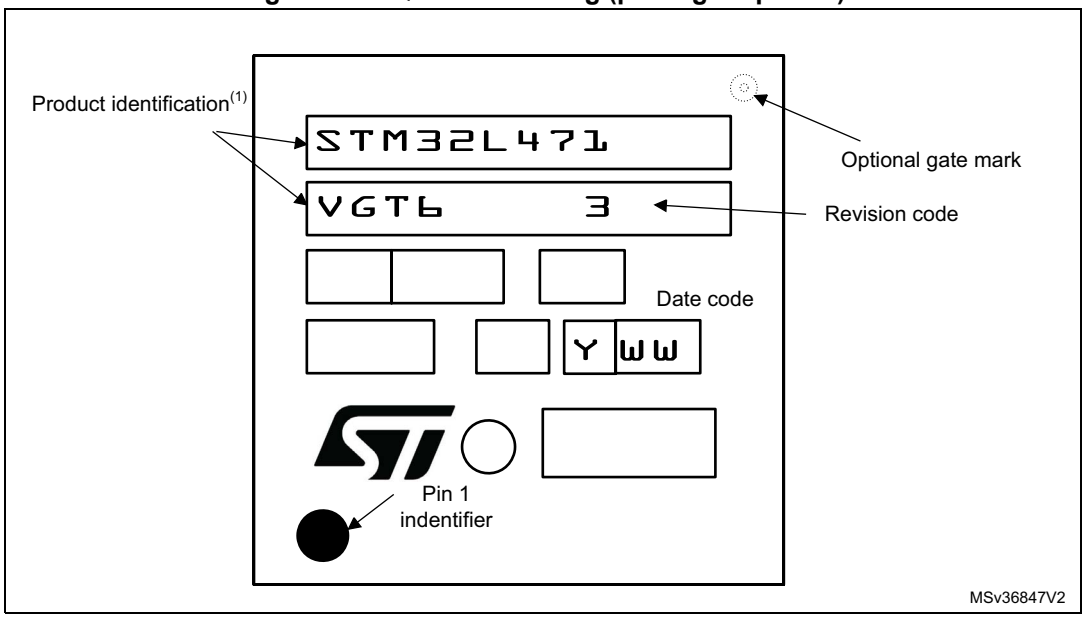


Table 104. UFBGA132 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5 mm
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm
Ball diameter	0.280 mm

Figure 56. LQFP100 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

8 Part numbering

Table 108. STM32L471xx ordering information scheme

Example: STM32 L 471 R G T 6 TR

Device family

STM32 = ARM® based 32-bit microcontroller

Product type

L = ultra-low-power

Device subfamily

471: STM32L471xx

Pin count

R = 64 pins

V = 100 pins

Q = 132 pins

Z = 144 pins

Flash memory size

E = 512 KB of Flash memory

G = 1 MB of Flash memory

Package

T = LQFP ECOPACK®2

I = UFBGA ECOPACK®2

Temperature range

6 = Industrial temperature range, -40 to 85 °C (105 °C junction)

7 = Industrial temperature range, -40 to 105 °C (125 °C junction)

3 = Industrial temperature range, -40 to 125 °C (130 °C junction)

Packing

TR = tape and reel

xxx = programmed parts